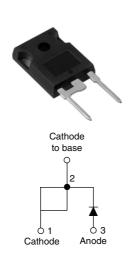
COMPLIANT



Vishay High Power Products

HEXFRED® Ultrafast Soft Recovery Diode, 16 A



TO-247AC modified

PRODUCT SUMMARY				
V_{R}	1200 V			
V _F at 16 A at 25 °C	3.0 V			
I _{F(AV)}	16 A			
t _{rr} (typical)	30 ns			
T _J (maximum)	150 °C			
Q _{rr} (typical)	260 nC			
dI _{(rec)M} /dt (typical) at 125 °C	76 A/μs			
I _{RRM} (typical)	5.8 A			

FEATURES

- Ultrafast recovery
- · Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- · Specified at operating conditions
- · Compliant to RoHS directive 2002/95/EC
- · Designed and qualified for industrial level

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION

HFA16PB120 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A continuous current, the HFA16PB120 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the $t_{\rm b}$ portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA16PB120 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	V _R		1200	V	
Maximum continuous forward current	I _F	T _C = 100 °C	16		
Single pulse forward current	I _{FSM}		190	Α	
Maximum repetitive forward current	I _{FRM}		64		
Maximum pawar discination	P _D	T _C = 25 °C	151	W	
Maximum power dissipation		T _C = 100 °C	60]	
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C	

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply

HFA16PB120PbF

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HEXFRED® Ultrafast Soft Recovery Diode, 16 A

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ		1200	-	-	
		I _F = 16 A		-	2.5	3.0	٧
Maximum forward voltage	V_{FM}	I _F = 32 A	See fig. 1	-	3.2	3.93	
		I _F = 16 A, T _J = 125 °C		-	2.3	2.7	
Maximum reverse	_	$V_R = V_R$ rated	See fig. 2	-	0.75	20	μΑ
leakage current	I _{RM}	$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 ^{\circ}\text{x} ^{\circ}\text{V}_R ^{\circ}\text{rated}$		-	375	2000	
Junction capacitance	C _T	V _R = 200 V	See fig. 3	-	27	40	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0 -		nΗ			

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
t_{rr} $I_F = 1.0 \text{ A, } dI_F/dt = 200 \text{ A/}\mu$) A/μs, V _R = 30 V	-	30	-		
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C	I _F = 16 A dI _F /dt = 200 A/μs V _R = 200 V	-	90	135	ns
000 lig. 0, 10	t _{rr2}	T _J = 125 °C		-	164	245	
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	5.8	10	А
See fig. 6	I _{RRM2}	T _J = 125 °C		-	8.3	15	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	260	675	
See fig. 7	Q _{rr2}	T _J = 125 °C		-	680	1838	nC
Peak rate of fall of recovery current during t _b	dI _{(rec)M} /dt1	T _J = 25 °C		-	120	-	A/us
See fig. 8	dI _{(rec)M} /dt2	T _J = 125 °C		-	76	-	7/μ5

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R _{thJC}		-	-	0.83	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.50	-	
Weight			-	2.0	-	g
Weight			-	0.07	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-247AC modified (JEDEC)	HFA16PB120		•	

For technical questions, contact: diodestech@vishay.com





HEXFRED® Vishay Ultrafast Soft Recovery Diode, 16 A

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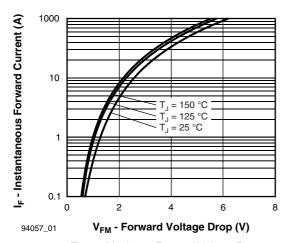


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

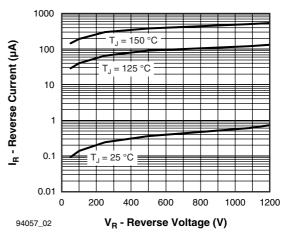


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

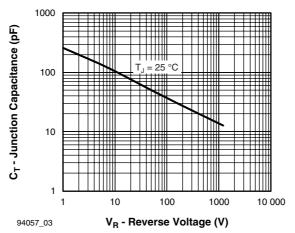


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

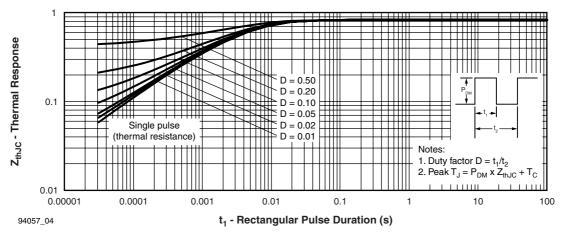


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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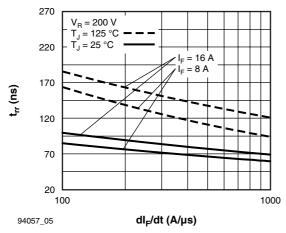


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt (Per Leg)

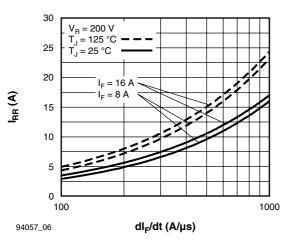


Fig. 6 - Typical Recovery Current vs. dI_F/dt (Per Leg)

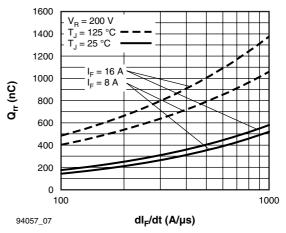


Fig. 7 - Typical Stored Charge vs. dI_F/dt (Per Leg)

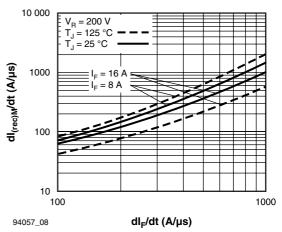


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt (Per Leg)



HEXFRED® Vishay High Power Products Ultrafast Soft Recovery Diode, 16 A

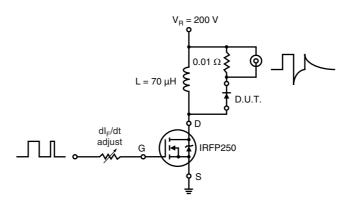
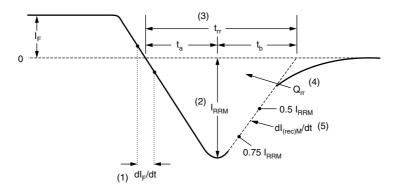


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

HFA16PB120PbF

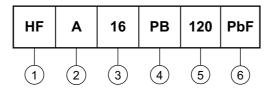
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HEXFRED® Ultrafast Soft Recovery Diode, 16 A



ORDERING INFORMATION TABLE

Device code



HEXFRED® family

Process designator: A = Electron irradiated

B = Platinum diffused

Current rating (16 = 16 A)

Package outline (PB = TO-247, 2 pins)

Voltage rating (120 = 1200 V) • None = Standard production

• PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95253</u>				
Part marking information	www.vishay.com/doc?95255			

www.vishay.com For technical questions, contact: diodestech@vishay.com

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